

MA2H735

Silicon epitaxial planer type

For high-frequency rectification

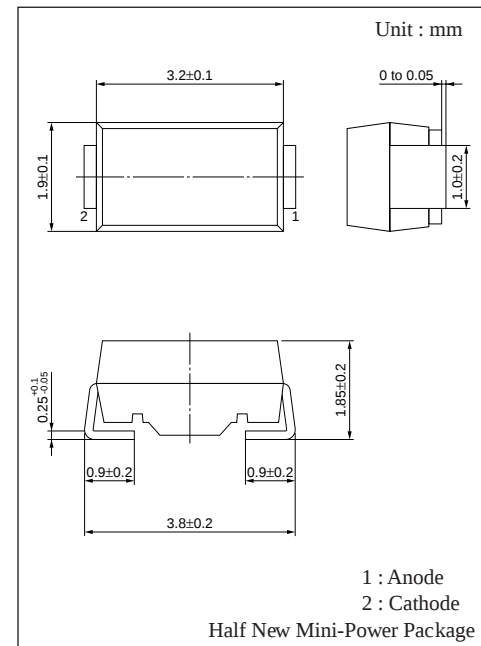
■ Features

- Small and thin half new mini-power package
- $I_{F(AV)}=1A$ rectification possible
- Low V_F (forward voltage) type : $V_F < 0.5V$ (at $I_F=1A$)

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}^*$	1	A
Non-repetitive peak forward surge current	I_{FSM}^*	30	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	- 40 to +125	°C

* 50Hz sine wave, one-cycle wave, high value (non-repetitive)

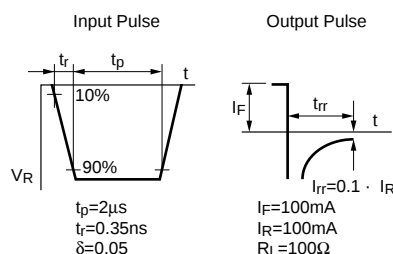
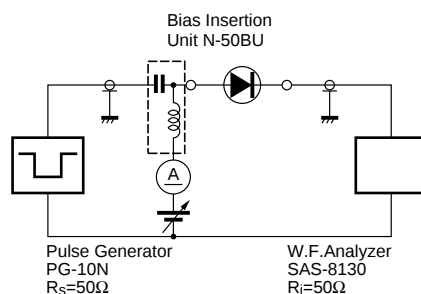


■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 30V$			1	mA
Forward voltage (DC)	V_F	$I_F = 1A$			0.50	V
Terminal capacitance	C_t	$V_R = 10V, f=1MHz$		50		pF
Reverse recovery time	t_{rr}^*	$I_F = I_R = 100mA$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$			30	ns

Note 1. Rated input/output frequency : 20MHz

2. * t_{rr} measuring circuit



■ Marking



